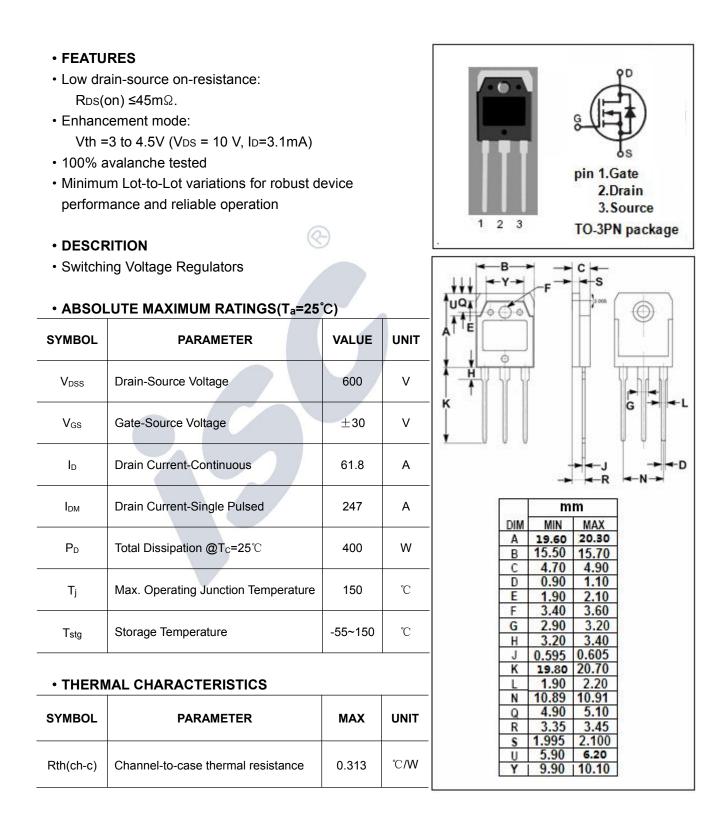


isc N-Channel MOSFET Transistor

TK62J60W5



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =10mA	600			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =10V; I _D =3.1mA	3		4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =30.9A			45	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			100	uA
V _{SDF}	Diode forward voltage	I _{DR} =61.8A, V _{GS} = 0 V			1.7	v



NOTICE:

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